

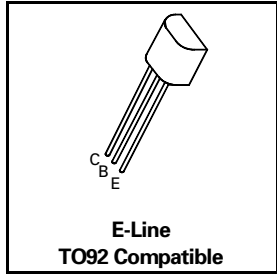
# PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

## ZTX752 ZTX753

### ISSUE 2 – JULY 94

#### FEATURES

- \* 100 Volt  $V_{CE0}$
- \* 2 Amp continuous current
- \* Low saturation voltage
- \*  $P_{tot}=1$  Watt



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX752	ZTX753	UNIT
Collector-Base Voltage	$V_{CBO}$	-100	-120	V
Collector-Emitter Voltage	$V_{CEO}$	-80	-100	V
Emitter-Base Voltage	$V_{EBO}$		-5	V
Peak Pulse Current	$I_{CM}$		-6	A
Continuous Collector Current	$I_C$		-2	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$ derate above $25^\circ\text{C}$	$P_{tot}$		1 5.7	W mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	$T_j; T_{stg}$		-55 to +200	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	ZTX752			ZTX753			UNIT	CONDITIONS.
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-100			-120			V	$I_C=-100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80			-100			V	$I_C=-10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			-5			V	$I_E=-100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$			-0.1 -10			-0.1 -10	$\mu\text{A}$ $\mu\text{A}$ $\mu\text{A}$ $\mu\text{A}$	$V_{CB}=-80\text{V}$ $V_{CB}=-100\text{V}$ $V_{CB}=-80\text{V}, T_{amb}=100^\circ\text{C}$ $V_{CB}=-100\text{V}, T_{amb}=100^\circ\text{C}$
Emitter Cut-Off Current	$I_{EBO}$			-0.1			-0.1	$\mu\text{A}$	$V_{EB}=-4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.17 -0.30	-0.3 -0.5			-0.17 -0.30 -0.5	V V	$I_C=-1\text{A}, I_B=-100\text{mA}^*$ $I_C=-2\text{A}, I_B=-200\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	-1.25			-0.9 -1.25	V	$I_C=-1\text{A}, I_B=-100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8	-1			-0.8 -1	V	$I_C=-1\text{A}, V_{CE}=-2\text{V}^*$

**ZTX752**  
**ZTX753**

**ELECTRICAL CHARACTERISTICS (at  $T_{amb} = 25^{\circ}C$ ).**

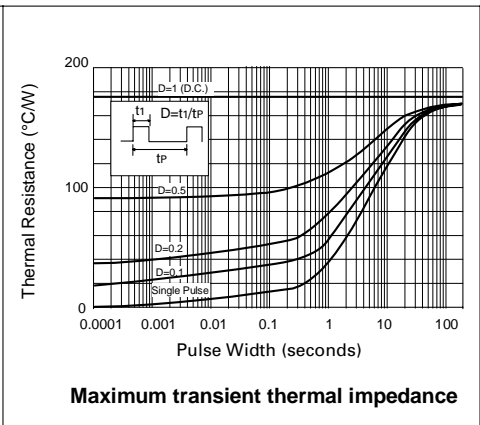
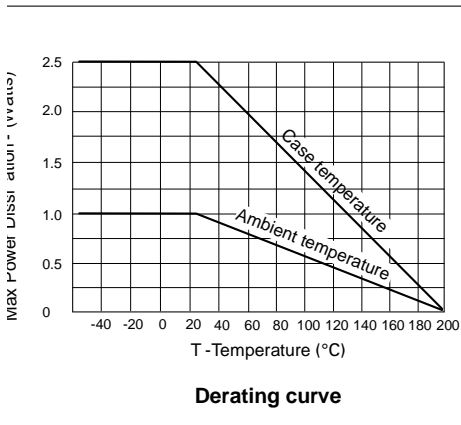
PARAMETER	SYMBOL	ZTX752			ZTX753			UNIT	CONDITIONS.
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Transition Frequency	$f_T$	100	140		100	140		MHz	$I_C=100mA, V_{CE}=5V$ $f=100MHz$
Switching Times	$t_{on}$		40			40		ns	$I_C=500mA, V_{CC}=10V$ $I_{B1}=I_{B2}=50mA$
	$t_{off}$		600			600		ns	
Output Capacitance	$C_{obo}$			30			30	pF	$V_{CB}=10V f=1MHz$

\*Measured under pulsed conditions. Pulse width=300 $\mu$ s. Duty cycle  $\leq$  2%

**THERMAL CHARACTERISTICS**

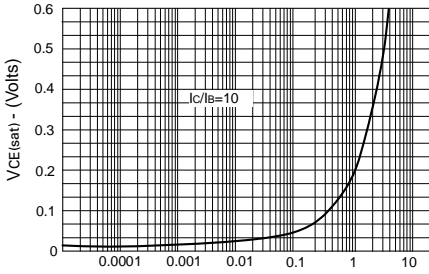
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient <sub>1</sub>	$R_{th(j-amb)1}$	175	$^{\circ}C/W$
Junction to Ambient <sub>2</sub>	$R_{th(j-amb)2} \dagger$	116	$^{\circ}C/W$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}C/W$

$\dagger$  Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.



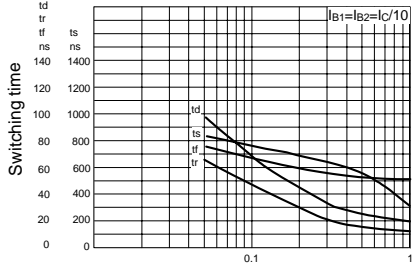
# ZTX752 ZTX753

## TYPICAL CHARACTERISTICS



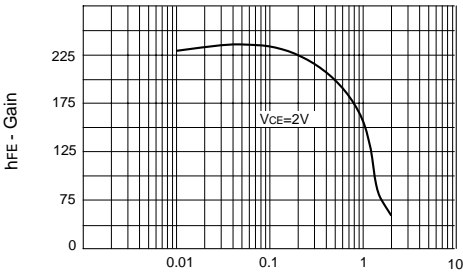
$I_C$  - Collector Current (Amps)

**$V_{CE(sat)}$  v  $I_C$**



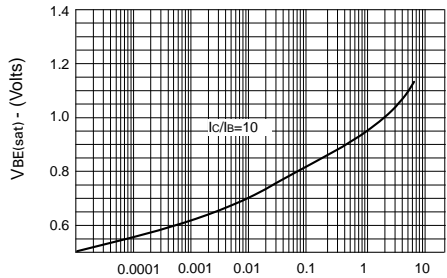
$I_C$  - Collector Current (Amps)

**Switching Speeds**



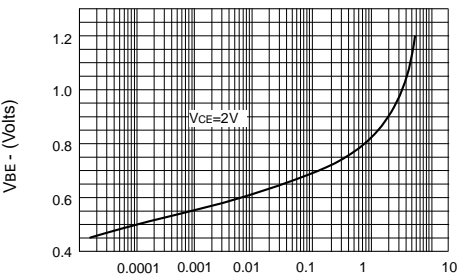
$I_C$  - Collector Current (Amps)

**$h_{FE}$  v  $I_C$**



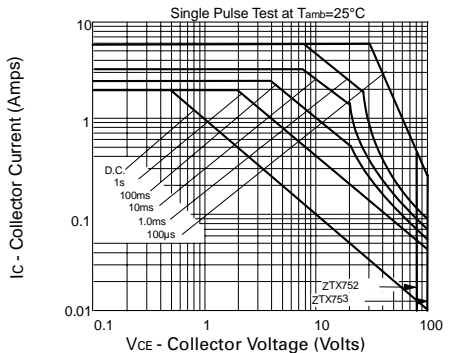
$I_C$  - Collector Current (Amps)

**$V_{BE(sat)}$  v  $I_C$**



$I_C$  - Collector Current (Amps)

**$V_{BE(on)}$  v  $I_C$**



**Safe Operating Area**